


**PRODUCT / PROCESS CHANGE NOTIFICATION**

**1. PCN basic data**

1.1 Company		STMicroelectronics International N.V
1.2 PCN No.	AMS/23/13946	
1.3 Title of PCN	AIS2IHTR: ST Rousset as additional FE plant.	
1.4 Product Category	Pls refer to the list	
1.5 Issue date	2023-02-20	

**2. PCN Team**

<b>2.1 Contact supplier</b>	
2.1.1 Name	ROBERTSON HEATHER
2.1.2 Phone	+1 8475853058
2.1.3 Email	heather.robertson@st.com
<b>2.2 Change responsibility</b>	
2.2.1 Product Manager	Andrea Mario ONETTI
2.1.2 Marketing Manager	Simone FERRI
2.1.3 Quality Manager	Michele CALDERONI

**3. Change**

<b>3.1 Category</b>	<b>3.2 Type of change</b>	<b>3.3 Manufacturing Location</b>
Transfer	Line transfer for a full process or process brick (process step, control plan, recipes) from one site to another site: Wafer fabrication	ST Crolles and ST Rousset as FE Plants

**4. Description of change**

	<b>Old</b>	<b>New</b>
4.1 Description	ST Crolles as FE plant	ST Rousset as additional FE plant
4.2 Anticipated Impact on form,fit, function, quality, reliability or processability?	No Impact	

**5. Reason / motivation for change**

5.1 Motivation	ST Rousset site as additional FE plant will increase the production capacity on the concerned products.
5.2 Customer Benefit	CAPACITY INCREASE

**6. Marking of parts / traceability of change**

6.1 Description	Dedicated FG code
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**7. Timing / schedule**

7.1 Date of qualification results	2023-03-03
7.2 Intended start of delivery	2024-01-09
7.3 Qualification sample available?	Upon Request

**8. Qualification / Validation**

8.1 Description	13946 AIS2IH_ASIC_Second_Source_Rousset_15022023.pdf		
8.2 Qualification report and qualification results	Available (see attachment)	Issue Date	2023-02-20

**9. Attachments (additional documentations)**

13946 Public product.pdf  
13946 AIS2IH\_ASIC\_Second\_Source\_Rousset\_15022023.pdf

10. Affected parts		
10. 1 Current		10.2 New (if applicable)
10.1.1 Customer Part No	10.1.2 Supplier Part No	10.1.2 Supplier Part No
	AIS2IHTR	

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# PCN #13946

## Activation of ST Rousset as additional diffusion plant for AIS2IH ASIC *VB60* die

STMicroelectronics  
MEMS Sensors Division - Analog and MEMS Group

February 15<sup>th</sup>, 2023

# Agenda

1 Change description

5 Validation Method

2 5M/1E Analysis

6 Conclusions

3 Manufacturing sites

4 Product Traceability

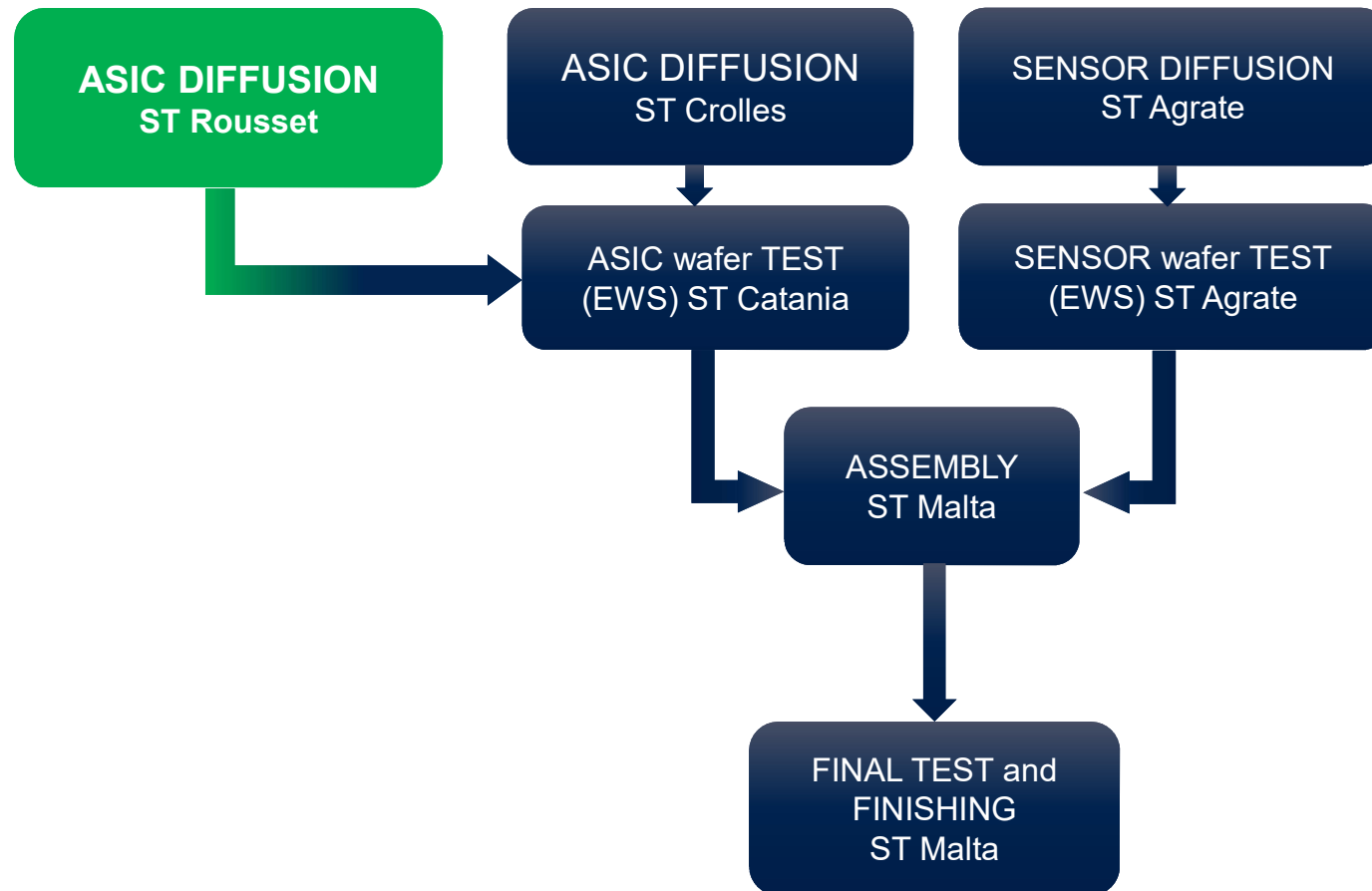
# Change description

- **Objective:**
  - Capacity increase by activation of ST Rousset as additional diffusion plant for AIS2IH ASIC *VB60* die.
- **Change details:**
  - *VB60* ASIC die used in AIS2IH product is currently diffused only in ST Crolles plant. With the change, ST Rousset will be activated as additional diffusion plant where *VB60* ASIC will be diffused.
  - The HCMOS9A technology, applied for *VB60* ASIC die, is being diffused in ST Rousset for more than 10 years and it is currently used in other ST Automotive products.
  - No other changes in the production flow are implemented, as confirmed below:
    - MEMS sensor diffusion plant is unchanged
    - EWS MEMS testing plant is unchanged
    - EWS ASIC testing plant is unchanged
    - Assembly plant is unchanged
    - Final Test and Finishing plant is unchanged
  - The activation of *VB60* ASIC in ST Rousset is planned by the beginning of Q1 2024

# 5M/1E Analysis

Change	Element	Control	Remarks
Additional diffusion plant : VB60 ASIC die in ST Rousset	<b>Machine</b>	Sharing the same equipment used for other ST Automotive products already qualified using same technology	The technology does not change, same mask set
	<b>Man</b>	Different production team	ST fab in Rousset is already qualified for automotive production and operators are well trained and certified
	<b>Material</b>	Bill of material (BOM)	No change
	<b>Measurement</b>	EWS and FT results and test distribution	No change
	<b>Method</b>	HCMOS9A technology (0.13μm process node)	No change. The HCMOS9A technology is already qualified and used in ST Rousset for more than 10 years
	<b>Environment</b>	ST fab in Rousset is qualified for automotive production	

# AIS2IH: Manufacturing sites





# AIS2IH: Product traceability

The activation of ST Rousset plant as diffusion plant for VB60 ASIC die:

- Will not impact on the Commercial Product name
- Will not impact the Ordering Code used by customers to allocate orders
- Will be traced in ST records as a **new Finished Good (FG) code with suffix –MDG/**

	CURRENT	NEW
ST Commercial Product	AIS2IHTR	AIS2IHTR
ST Marking	No change	No change
ST Finished Good (T&R)	AIS2IHTR-MD2/	AIS2IHTR-MDG/

# Change Validation plan

- Considering that:
  - Both ST Crolles and ST Rousset factories are qualified to produce automotive devices.
  - Both ST Crolles and ST Rousset factories have active production lines on the HCMOS9A technology, which is used in billion of units across several market domains, including automotive .
- The following 4-steps validation activity has been performed to confirm that the two diffusion fabs are aligned on the specific production for AIS2IH:
  1. Reliability verification of the VB60 ASIC diffused in Rousset
  2. Characterization activity
  3. Verification at the Final Test of 50k units from 3 different lots processed in ST Rousset and St Crolles, with final check of test yields and distribution of key parameters.
- Acceptance criteria are defined as follows:
  - Good alignment of test distribution of key parameters on 50Ku (see next slide for the acceptance criteria)
  - Yield analysis
  - 0 confirmed rejects at QA ( with QA step performed at 100%)



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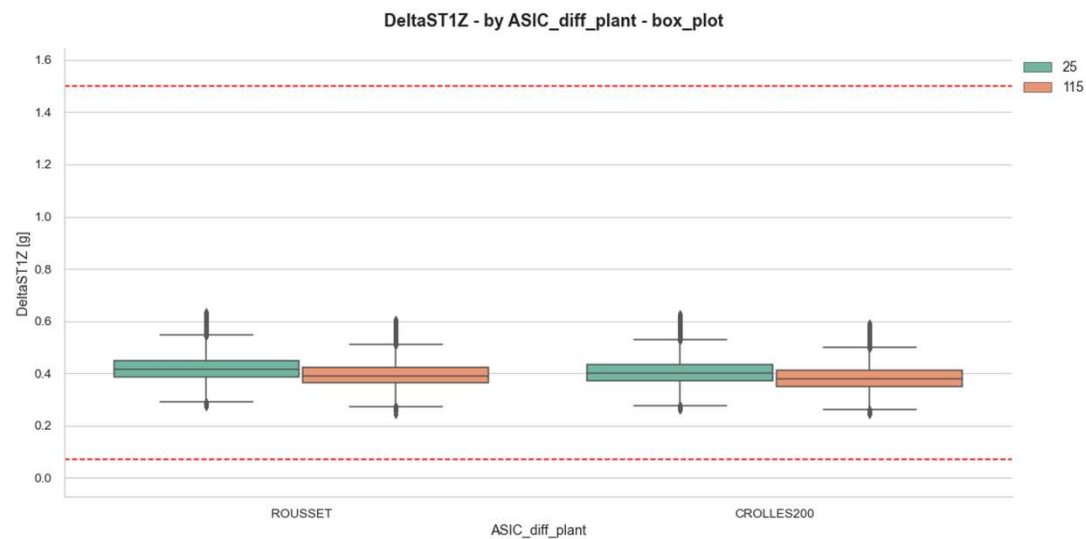
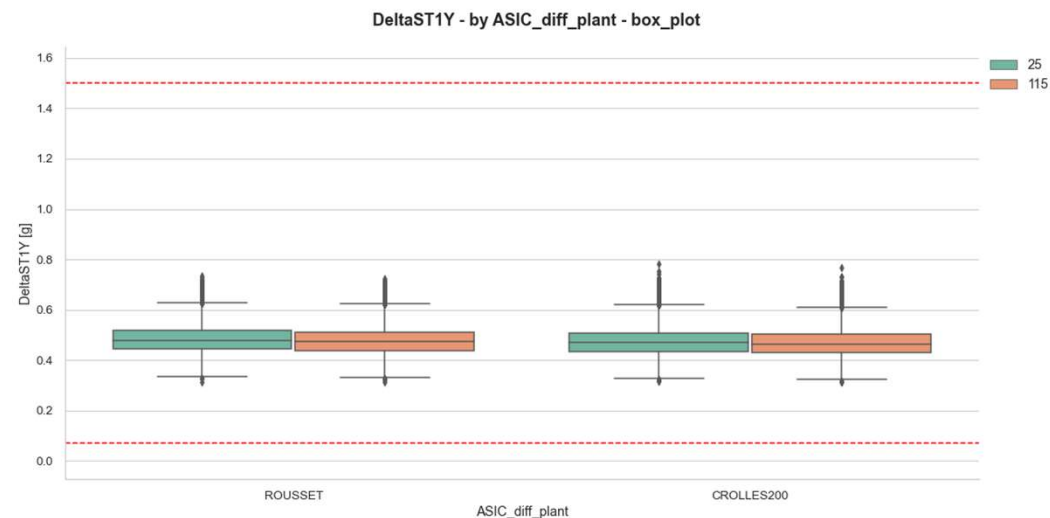
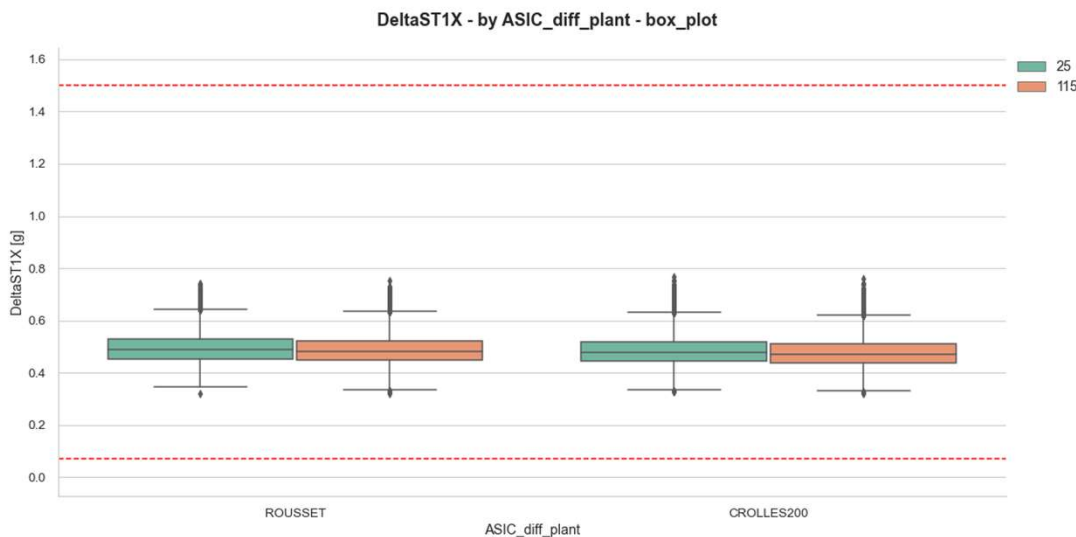
# Final Test data analysis on key parameters: Amb and Hot

# Final Test data analysis: Acceptance criteria

Parameter	Acceptance Criteria
Offset Lp / Hp	Difference between average values on the two plants < 15mg Difference between standard deviations on the two plants in % < 30%
Sensitivity Lp / Hp	Difference between average values on the two plants in % < 2% Difference between standard deviations on the two plants in % < 15%
I <sub>dd</sub> in Power Down	Difference between average values on the two plants i < 30 na Difference between standard deviations on the two plants in % < 40% for Amb Difference between standard deviations on the two plants in % < 60% for Hot
I <sub>dd</sub> at 100Hz LP/ I <sub>dd</sub> 200Hz	Difference between average values on the two plants in % < 20% Difference between standard deviations on the two plants in % < 20%
Seltest	Difference between average values on the two plants < 50 mg Difference between standard deviations on the two plants in % < 15%

Acceptance criteria are based on product features (IC with electronics and mechanics), equipment knowledge and analogy vs similar cases (experience), considering both the quantity involved and the temperature effect

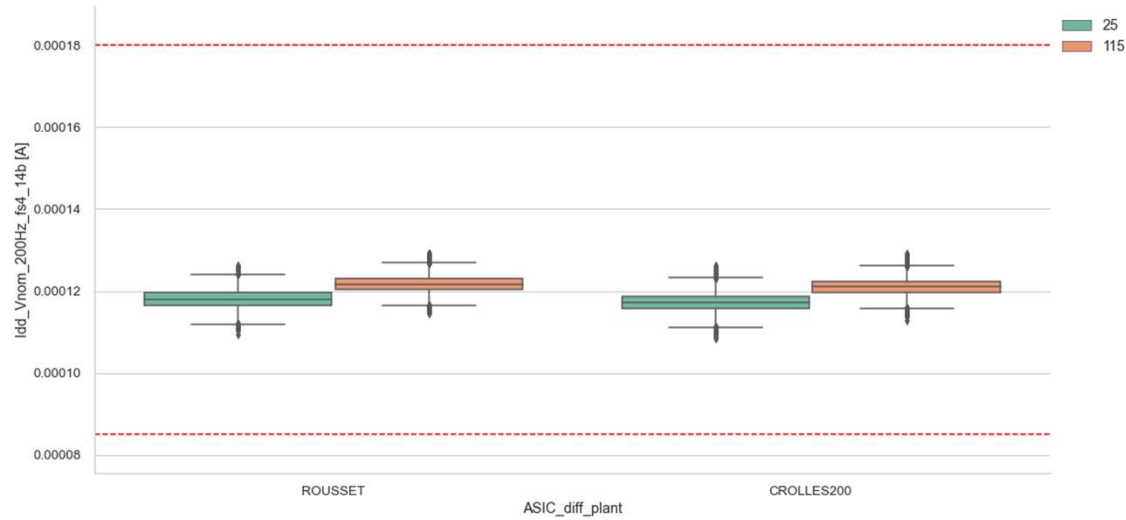
# Parameter: Delta Self Test positive



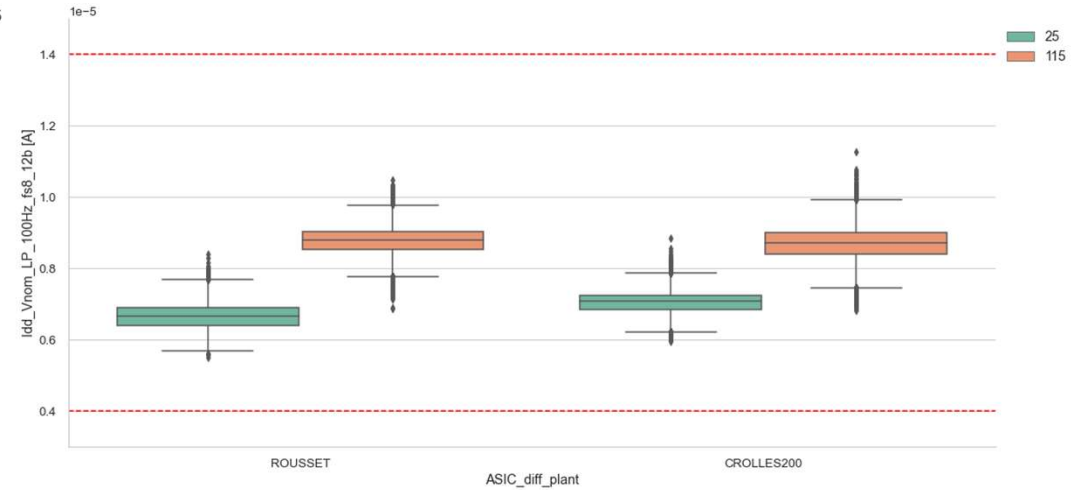
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# Parameter: Current consumption

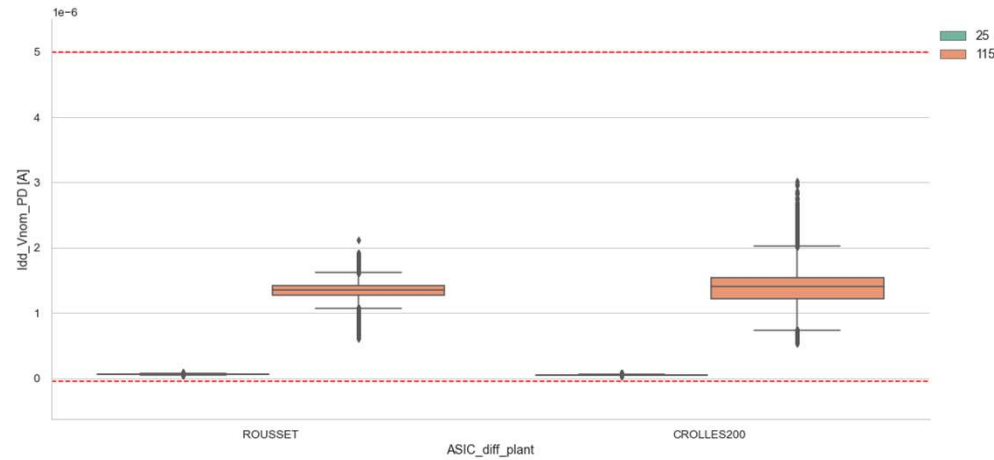
Idd\_Vnom\_200Hz\_fs4\_14b - by ASIC\_diff\_plant - box\_plot



Idd\_Vnom\_LP\_100Hz\_fs8\_12b - by ASIC\_diff\_plant - box\_plot



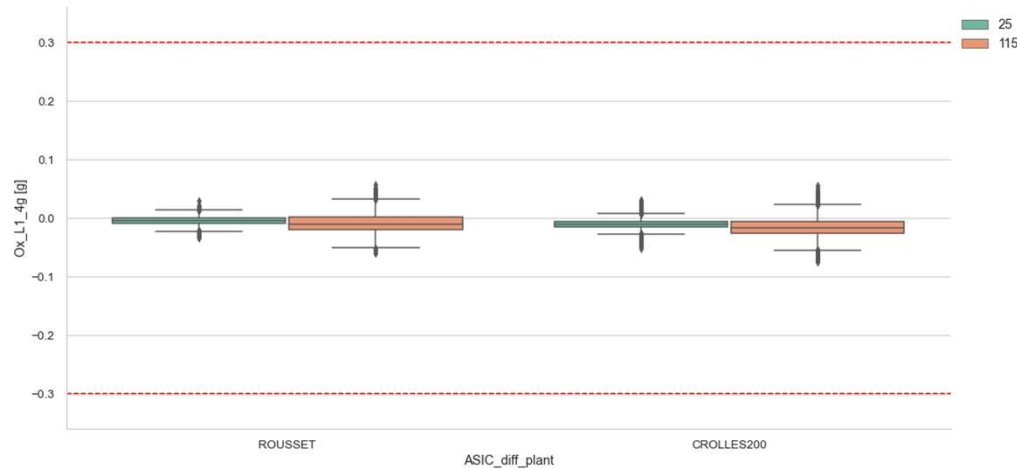
Idd\_Vnom\_PD - by ASIC\_diff\_plant - box\_plot



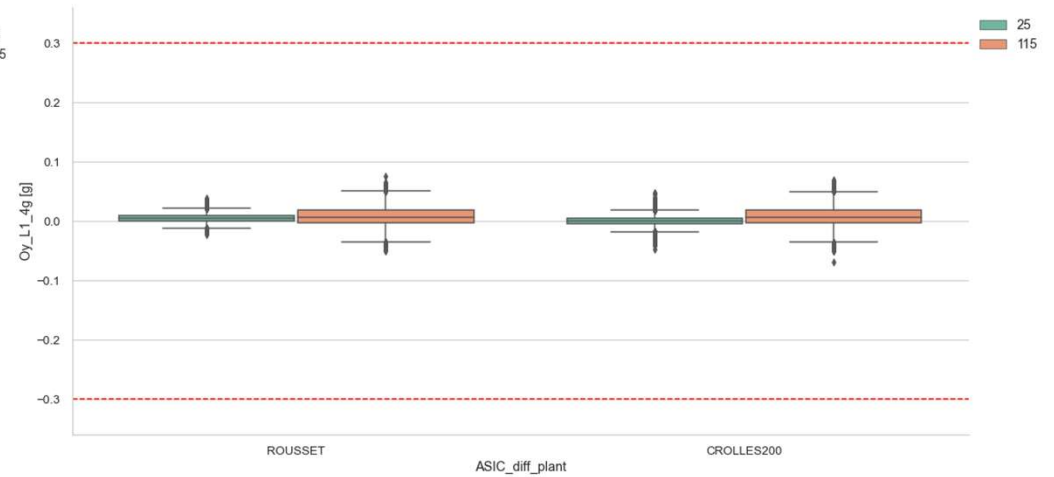
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# Parameter: Offset low performance

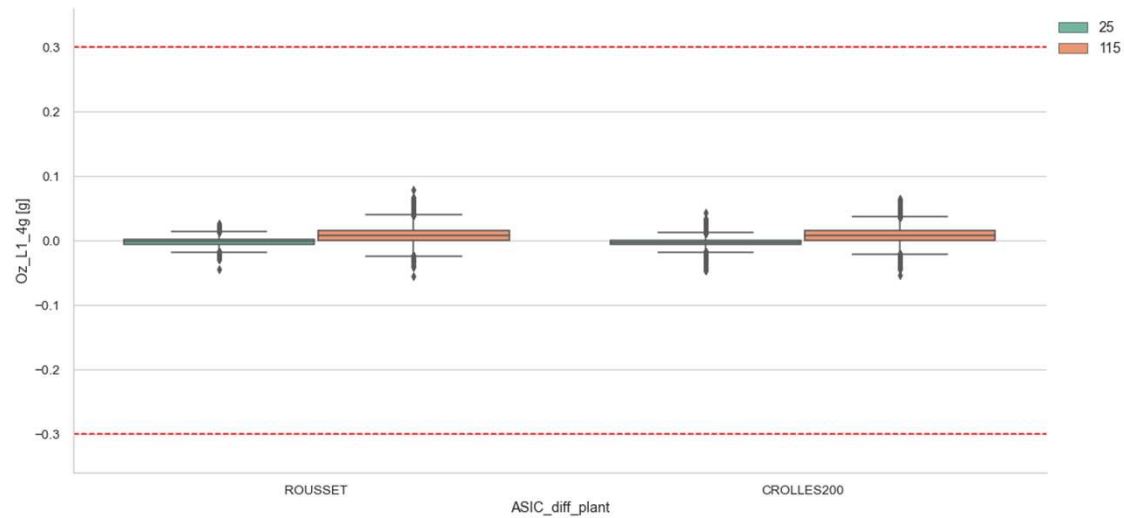
Ox\_L1\_4g - by ASIC\_diff\_plant - box\_plot



Oy\_L1\_4g - by ASIC\_diff\_plant - box\_plot



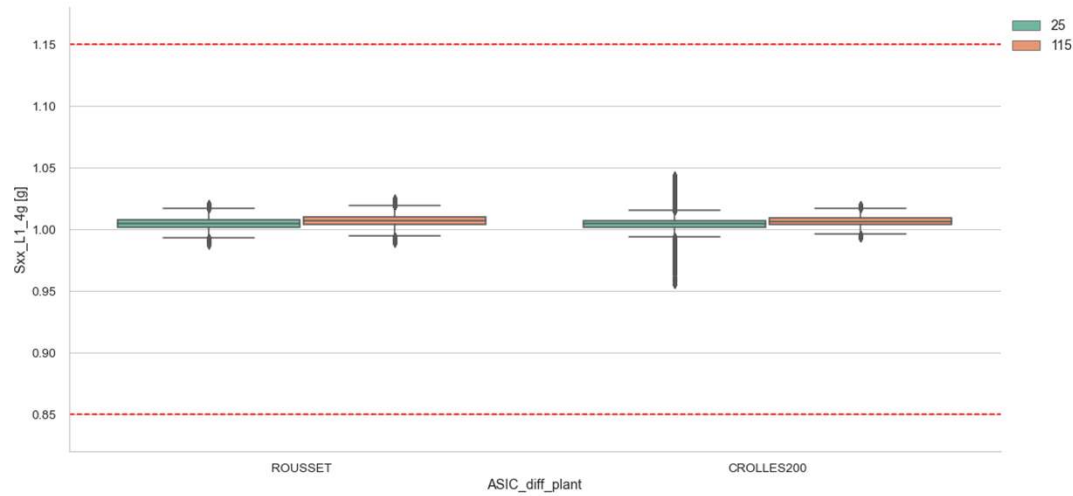
Oz\_L1\_4g - by ASIC\_diff\_plant - box\_plot



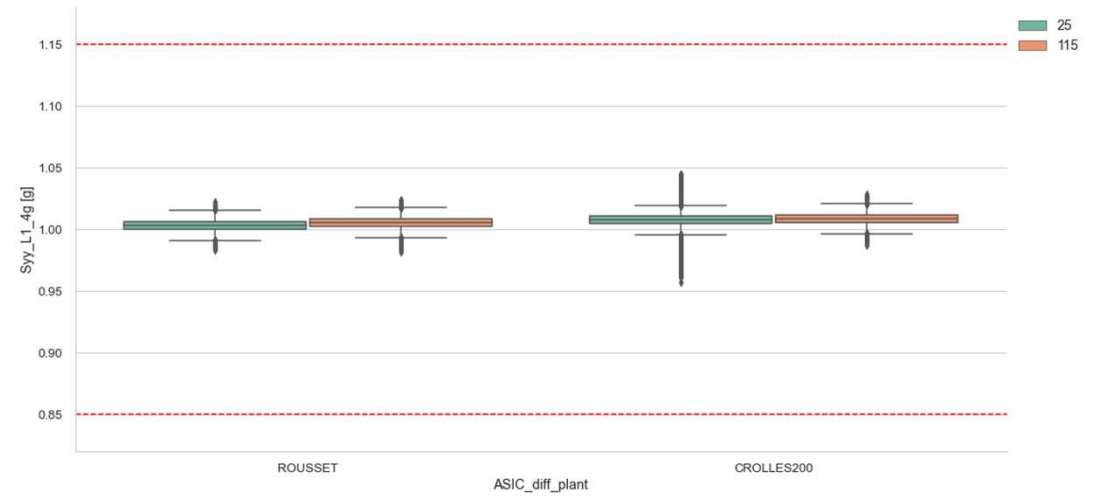
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# Parameter: Sensitivity low performance

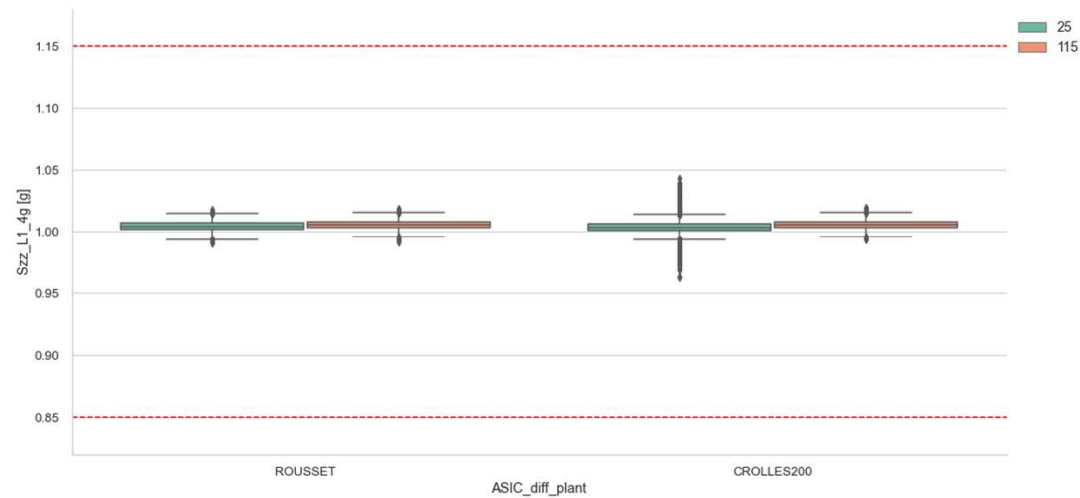
Sxx\_L1\_4g - by ASIC\_diff\_plant - box\_plot



Syy\_L1\_4g - by ASIC\_diff\_plant - box\_plot



Szz\_L1\_4g - by ASIC\_diff\_plant - box\_plot

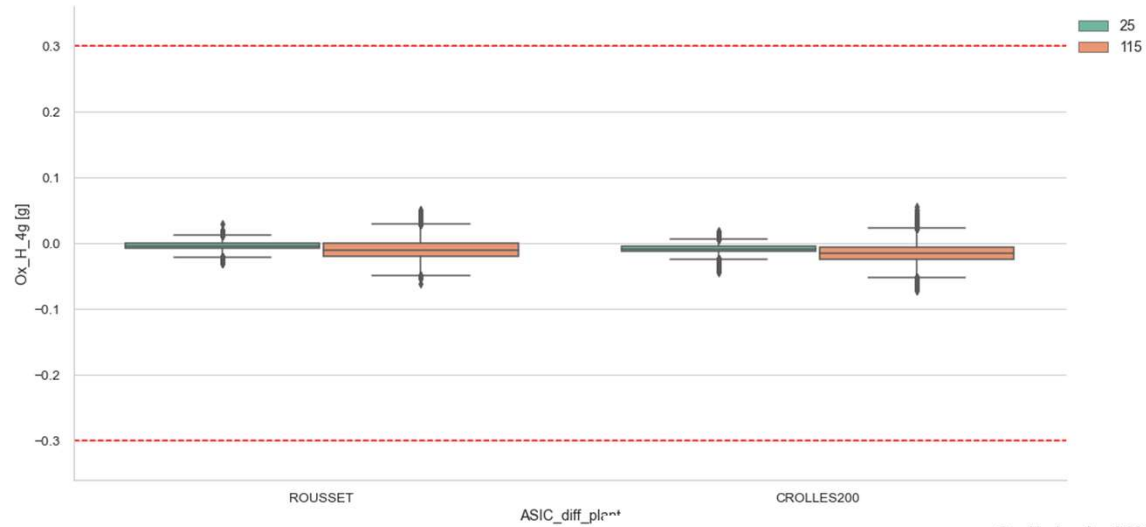


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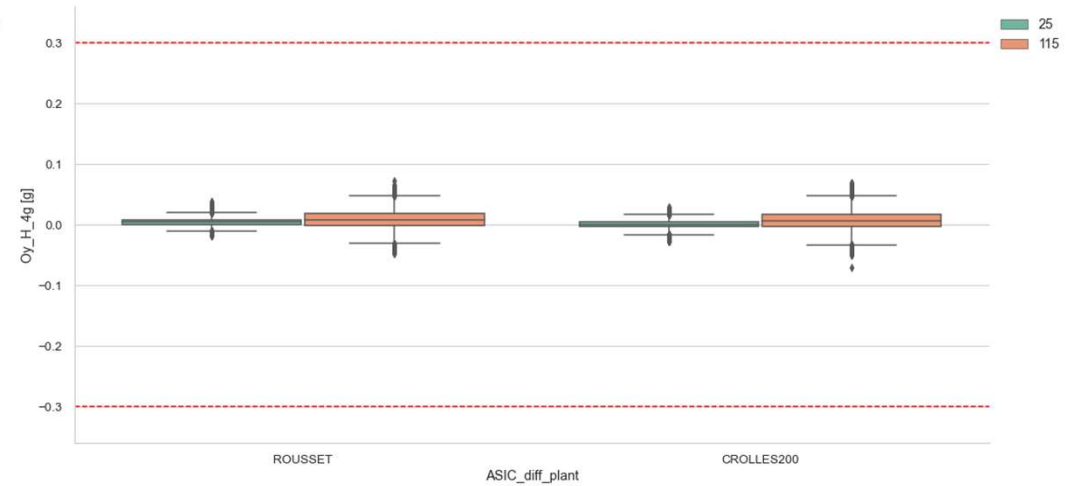


# Parameter: Offset high performance

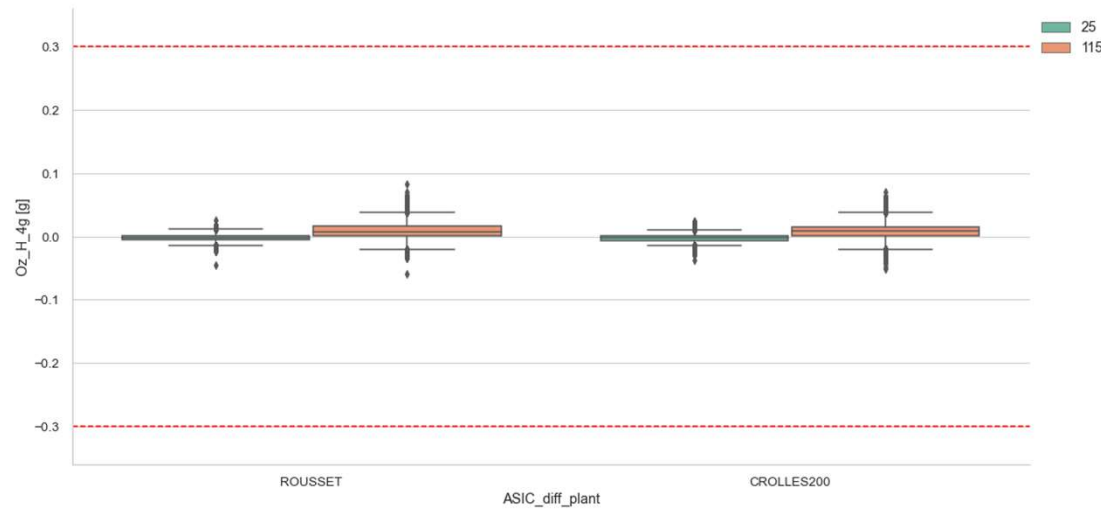
Ox\_H\_4g - by ASIC\_diff\_plant - box\_plot



Oy\_H\_4g - by ASIC\_diff\_plant - box\_plot



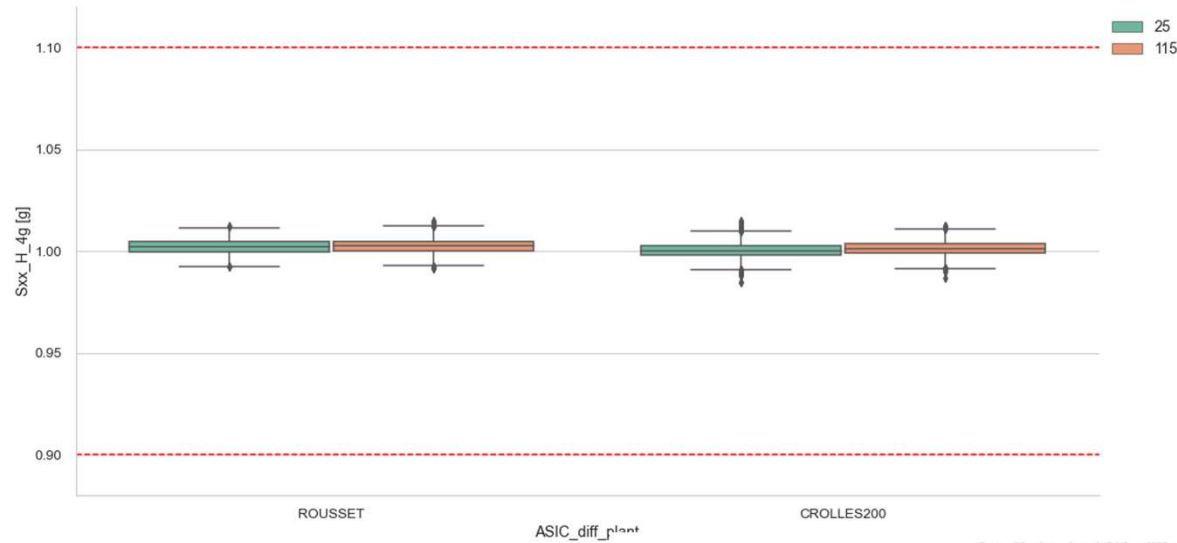
Oz\_H\_4g - by ASIC\_diff\_plant - box\_plot



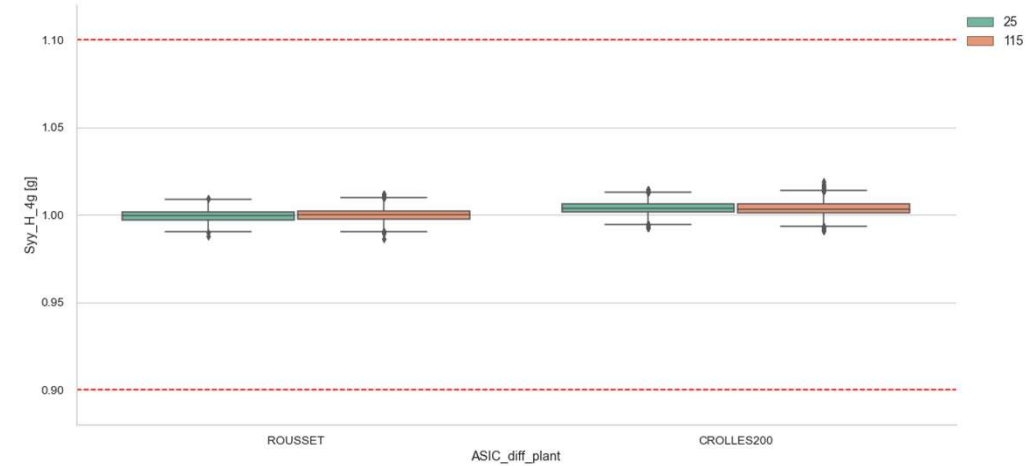
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# Parameter: Sensitivity high performance

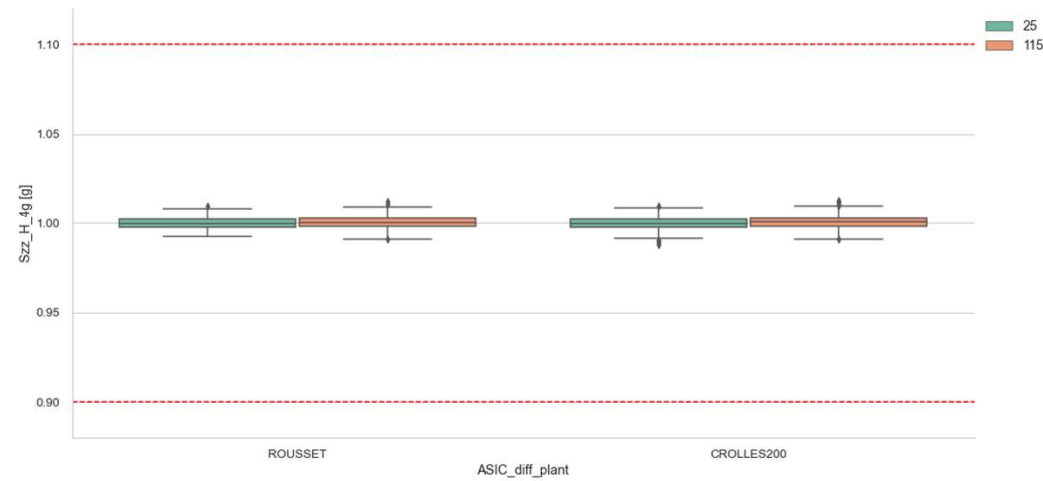
Sxx\_H\_4g - by ASIC\_diff\_plant - box\_plot



Syy\_H\_4g - by ASIC\_diff\_plant - box\_plot



Szz\_H\_4g - by ASIC\_diff\_plant - box\_plot



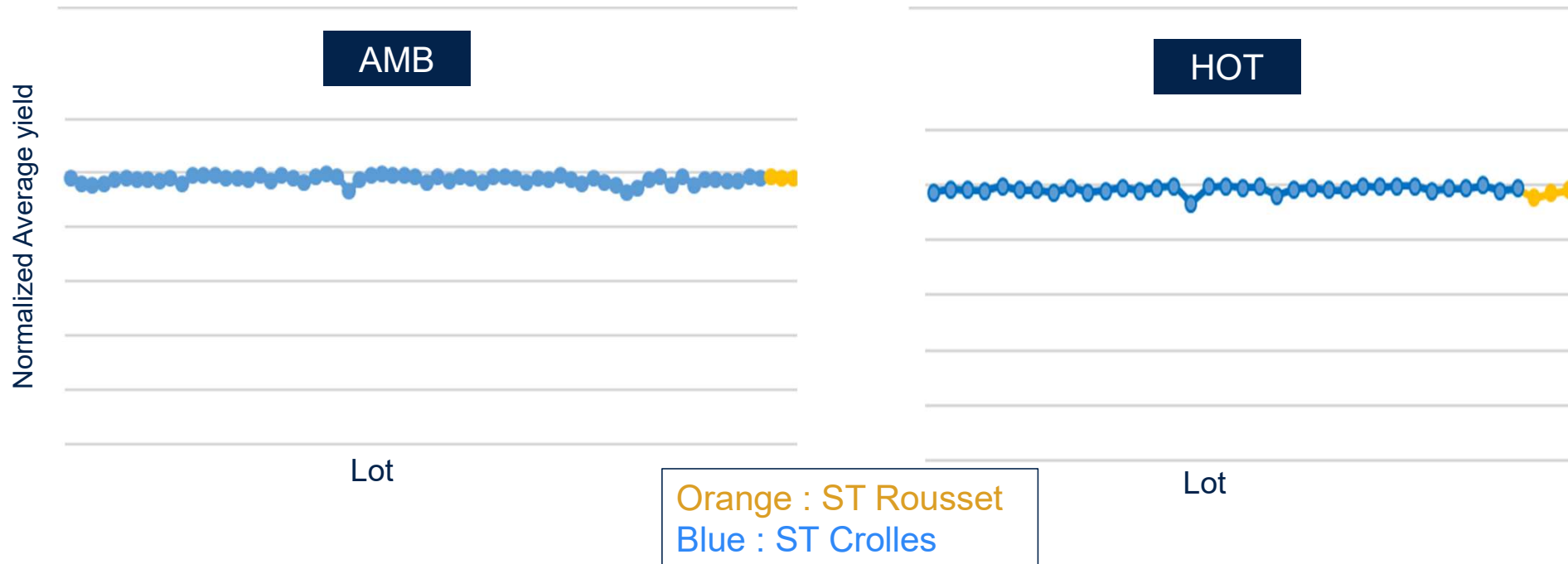
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# Final Test yield data analysis: Amb and Hot

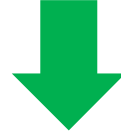
# Final Test yield data analysis: Amb and Hot



**Final test yields observed on devices embedding the ASIC diffused in ST Rousset are comparable to those seen on the device with the ASIC from ST Crolles.**

# Conclusions

- Considering that:
  1. The successful completion of the reliability activity
  2. The successful completion of the characterization activity
  3. The successful completion of the verification at the Final Test of 50k units from 3 different lots processed in ST Rousset and St Crolles, with final check of test yields and distribution of key parameters



**ST Rousset diffusion plant has been qualified for the production of VB60 ASIC die**

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PCN Reference : AMS/23/13946

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AIS2IHTR		
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